



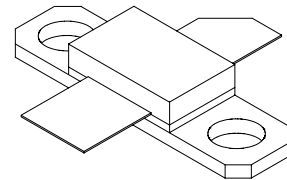
UPF1030

30W, 1.0 GHz, 26V Broadband RF Power N-Channel Enhancement-Mode Lateral MOSFET

This device is designed for base station applications up to frequencies of 1.0 GHz. Rated with a minimum output power of 30W, it is ideal for CDMA, TDMA, GSM, FM, Single or Multi-Carrier Power Amplifiers in Class A or AB operation.

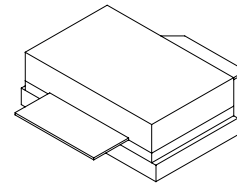
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- ALL GOLD metal system for highest reliability.
- Industry standard package.
- Low intermodulation distortion of -30dBc at 30W (PEP).



Package Type 440095

PN: UPF1030F



Package Type 440134

PN: UPF1030P

Maximum Ratings

Rating	Symbol	Value	Unit
Drain to Source Voltage, gate connected to source	BV_{DSS}	65	Volts
Gate to Source Voltage	BV_{GSS}	+/- 20	Volts
Total Device Dissipation @ Tcase = 70°C Derate above 70°C	P_D	65.0 0.5	Watts W/°C
Storage Temperature Range	T_{STG}	-65 to +150	°C
Operating Junction Temperature	T_J	200	°C

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Thermal Characteristics

Characteristics	Symbol	Typical	Unit
Thermal Resistance, Junction to Case	θ_{jc}	1.6	°C/W

Electrical DC Characteristics ($T_C=25^\circ\text{C}$ unless otherwise specified)

Rating	Symbol	Min	Typ	Max	Unit
Drain to Source Voltage, gate connected to source ($V_{GS} = 0, I_{DS} = 1\text{mA}$)	BV_{DSS}	65	-	-	Volts
Drain to Source Leakage current ($V_{DS} = 28\text{V}, V_{GS} = 0$)	I_{DSS}	-	-	1.0	mA
Gate to Source Leakage current ($V_{GS} = 20\text{V}, V_{DS} = 0$)	I_{GSS}	-	-	1.0	μA
Threshold Voltage ($V_{DS} = 10\text{V}, I_{DS} = 1\text{mA}$)	V_{TH}	2.0	3.5	5.0	Volts
Gate Quiescent Voltage ($V_{DS} = 26\text{V}, I_{DS} = 200\text{mA}$)	$V_{GS(on)}$	3.0	4.0	6.0	Volts
Drain to Source On Voltage ($V_{GS} = 10\text{V}, I_{DS} = 1\text{A}$)	$V_{DS(on)}$	-	0.28	-	Volts
Forward Transconductance ($V_{DS} = 10\text{V}, I_D = 5\text{A}$)	G_M	1.4	1.8	-	S

AC Characteristics (T_C=25°C unless otherwise specified)

Rating	Symbol	Min	Typ	Max	Unit
Input Capacitance (V _{DS} =26V, V _{GS} =0V, freq= 1MHz)	C _{ISS}	-	44	-	pF
Output capacitance (V _{DS} = 26V, V _{GS} =0V, freq= 1MHz)	C _{OSS}	-	28	-	pF
Feedback capacitance (V _{DS} =26V, V _{GS} =0V, freq= 1MHz)	C _{RSS}	-	1.2	-	pF

RF and Functional Tests (T_C=25°C unless otherwise specified, Cree Microwave Broadband Fixture)

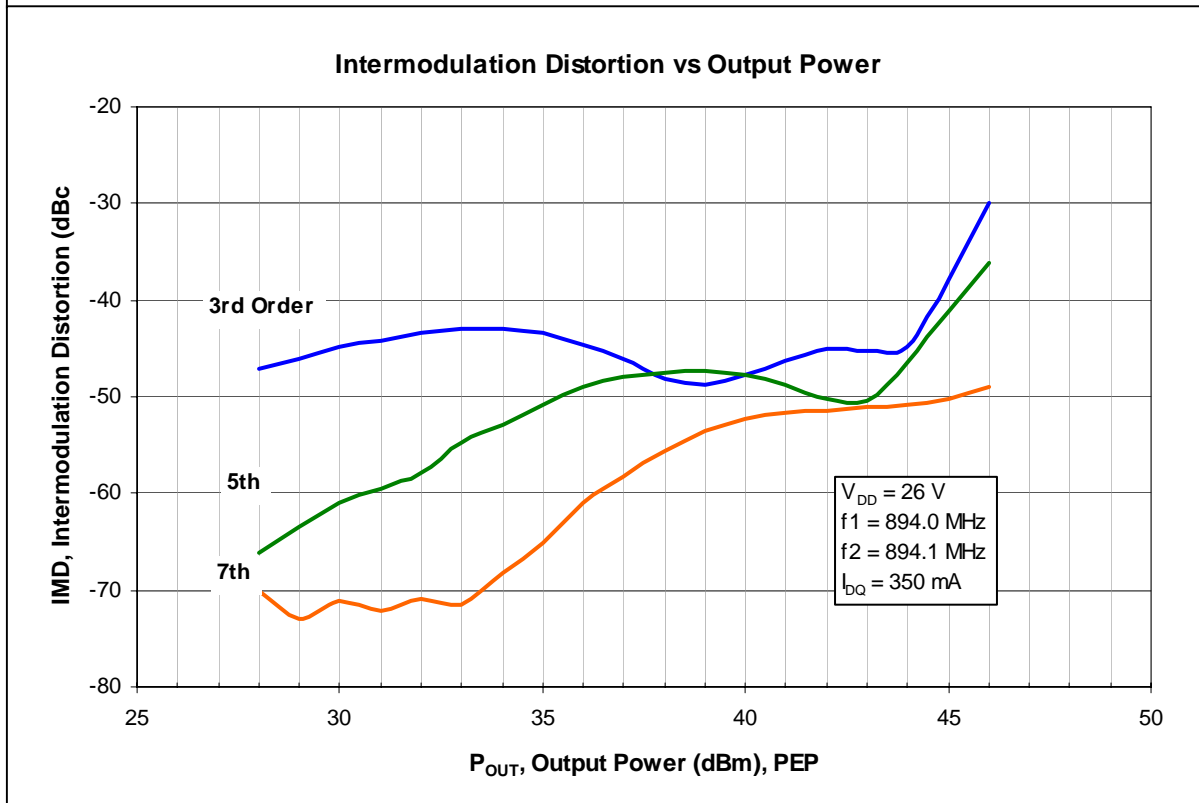
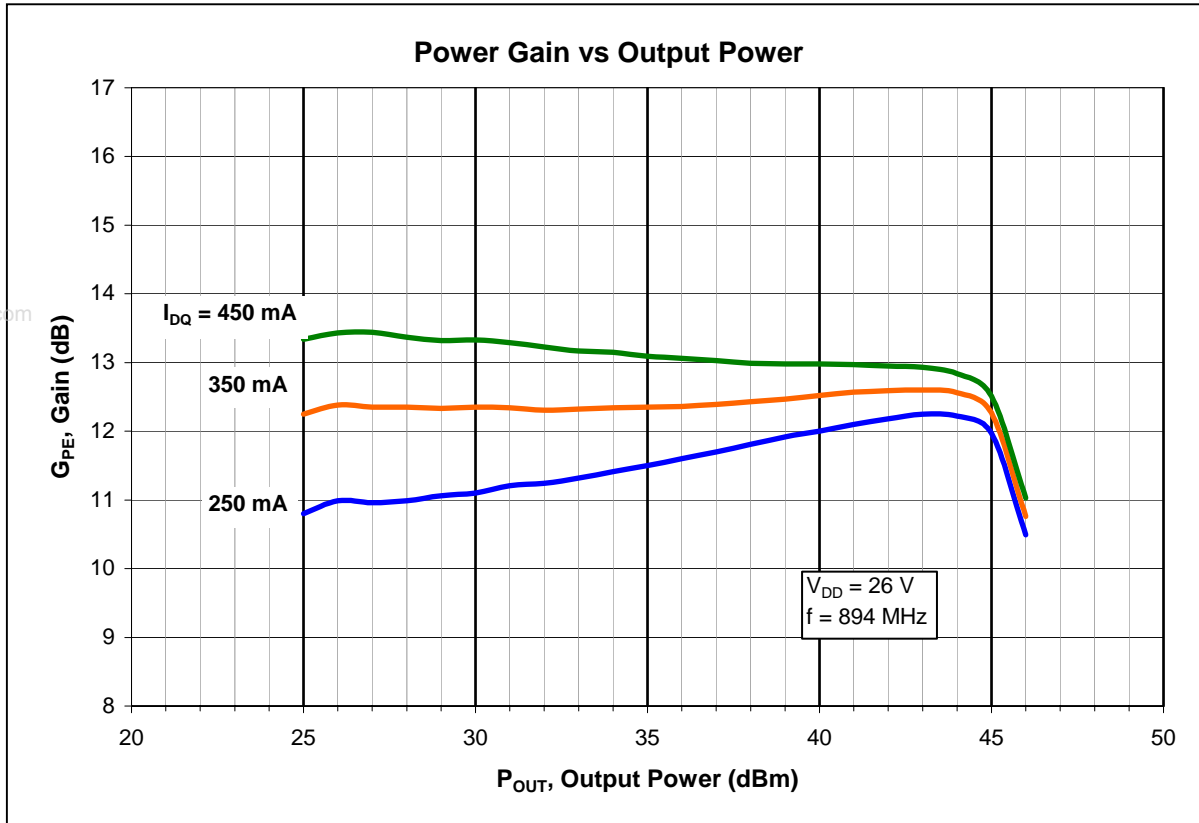
Rating	Symbol	Min	Typ	Max	Unit
Linear Power Gain, Single Tone (V _{DS} =26V, I _{DQ} =350mA, P _{OUT} =5W, f=894 MHz)	G _L	13.0	14.5	-	dB
Compressed Power Gain, Single Tone (V _{DS} =26V, I _{DQ} =350mA, P _{OUT} =30W, f=894 MHz)	G _P	12.0	14.0	-	dB
Drain Efficiency, Single Tone (V _{DS} =26V, I _{DQ} =350mA, P _{OUT} =30W, f=894 MHz)	η _D	45	52	-	%
Intermodulation Distortion, Two Tone (V _{DS} =26V, I _{DQ} =350mA, P _{OUT} =30W PEP f1=894 MHz, f2=894.1MHz)	IMD	-	-35	-30	dBc
Load Mismatch Tolerance (V _{DS} =26V, I _{DQ} =350mA, P _{OUT} =30W, f=894 MHz)	VSWR*	10:1	-	-	Ψ

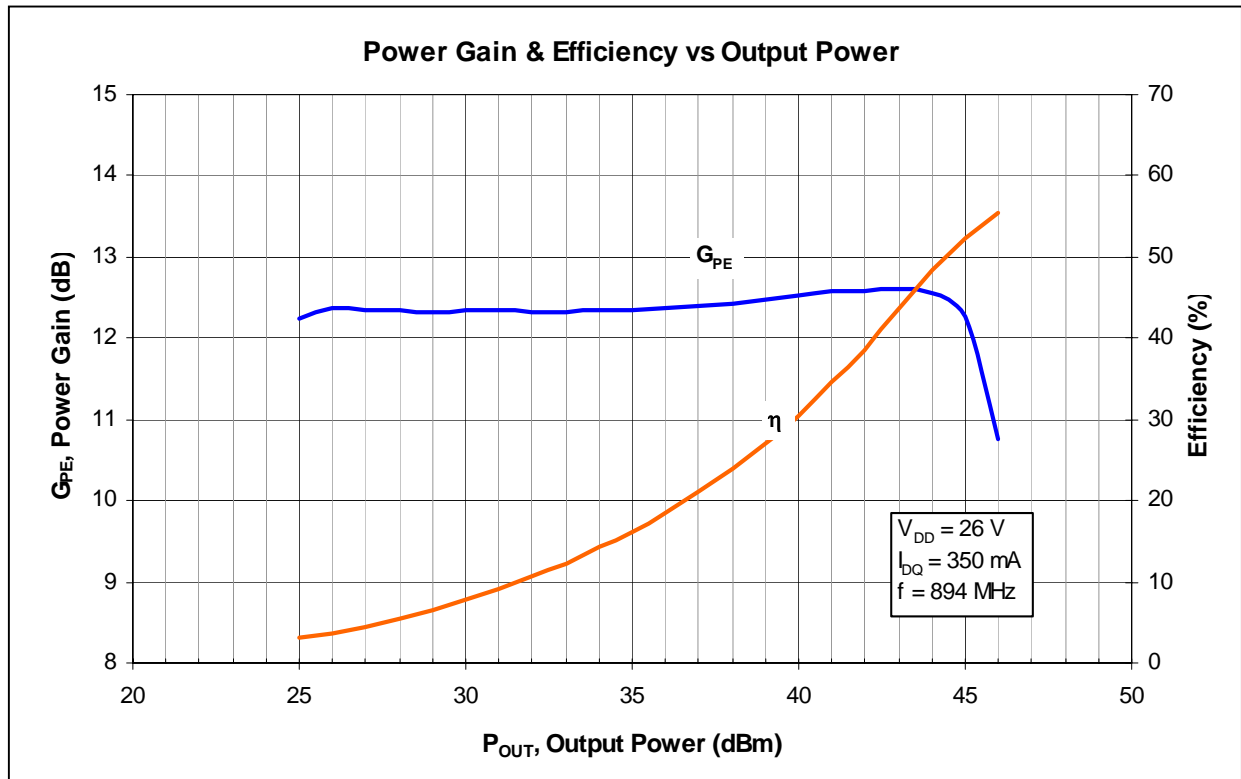
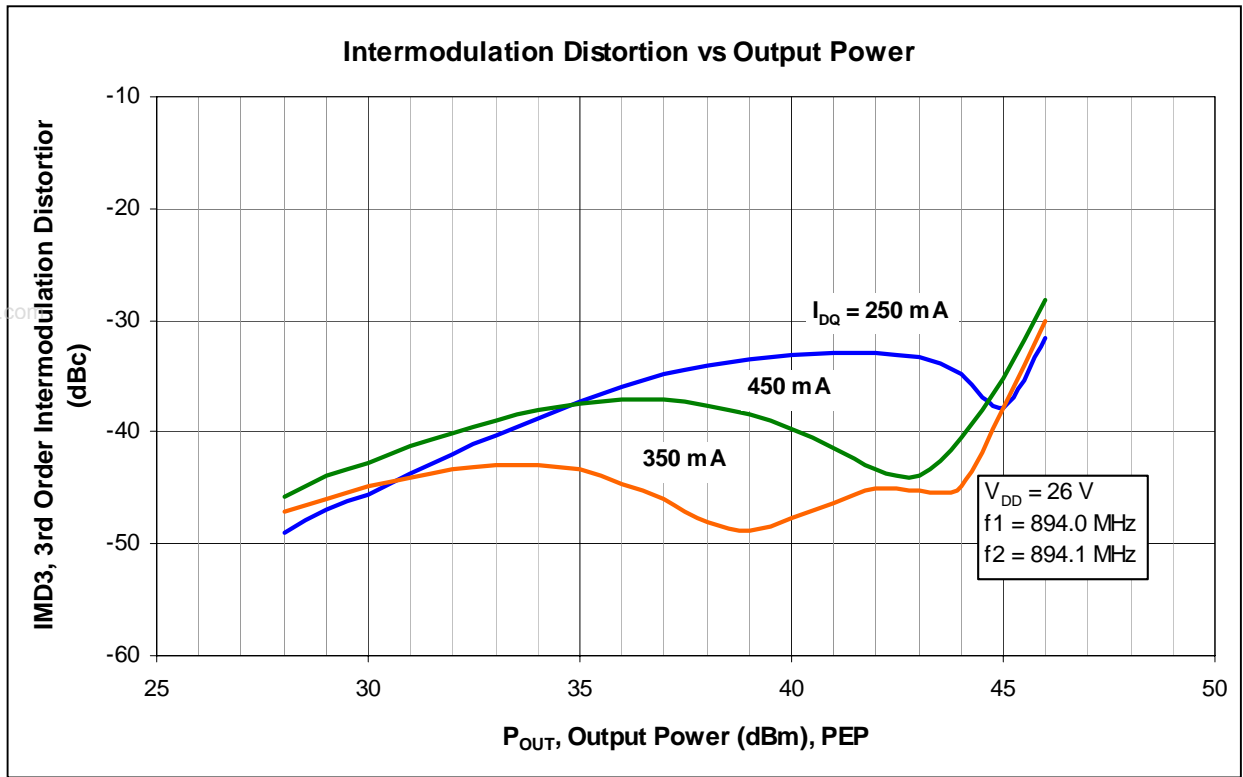
Note (unless otherwise specified):

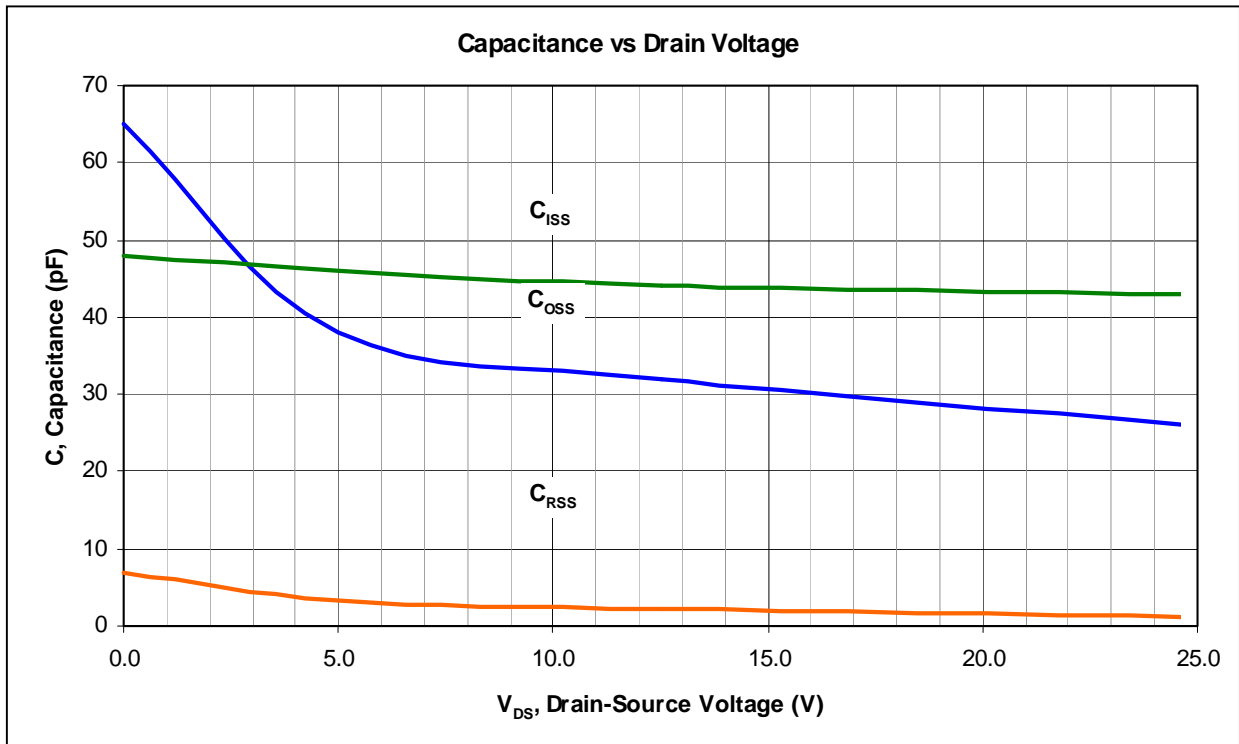
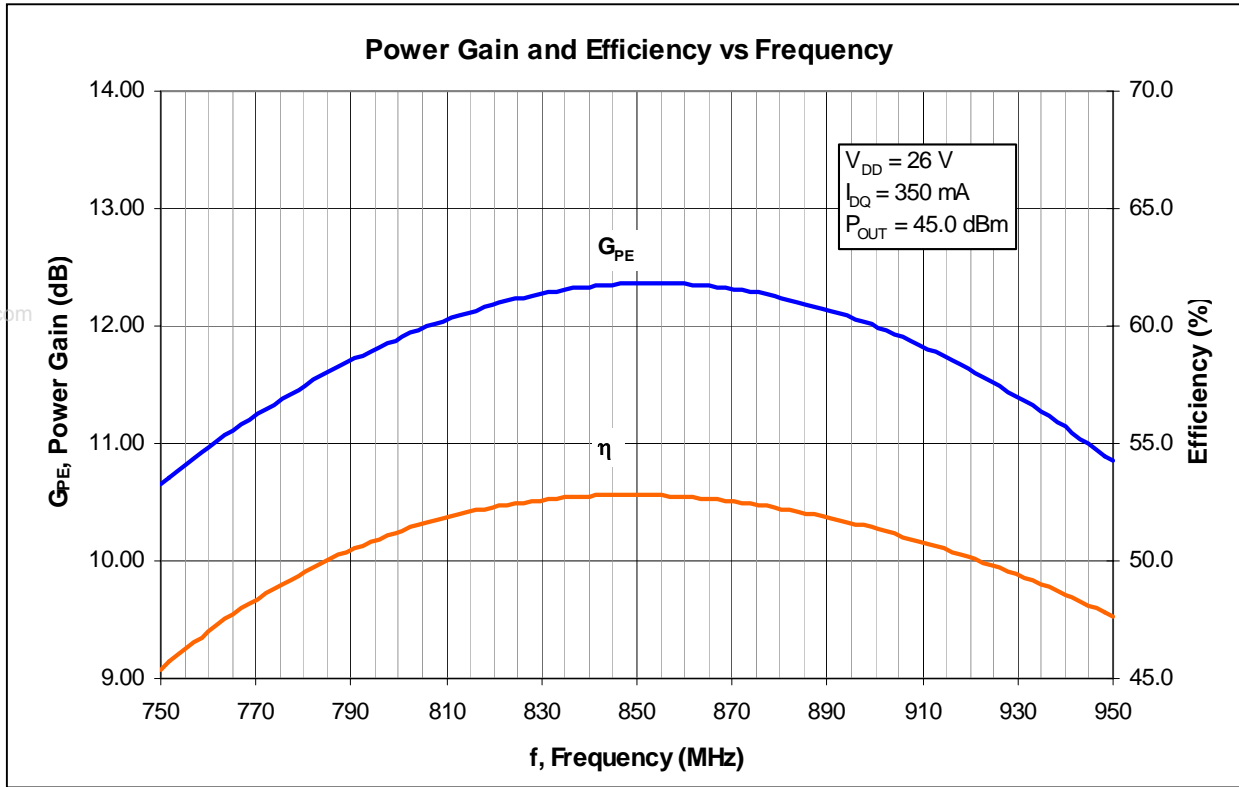
1. Source and load impedance shall be 50 ohms.

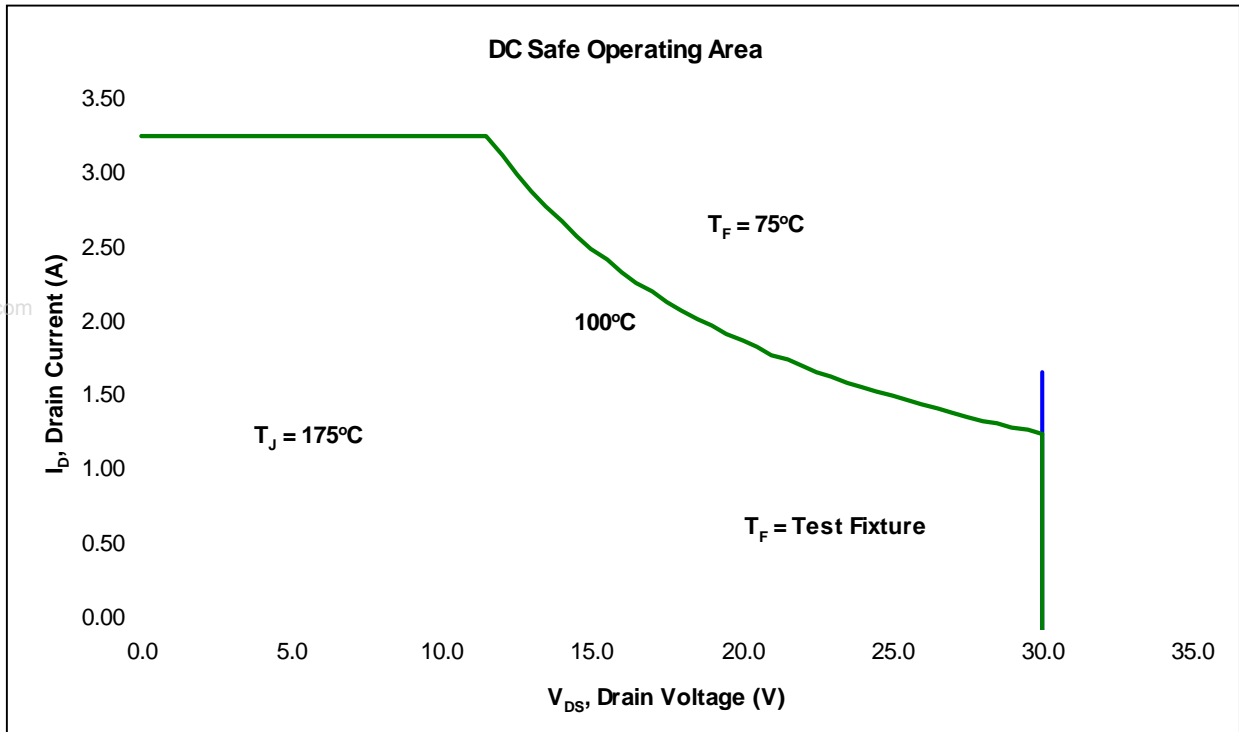
*No degradation in device performance after test.

CAUTION - MOS Devices are susceptible to damage from Electrostatic Discharge (ESD). Appropriate precautions in handling, packaging and testing MOS devices must be observed.

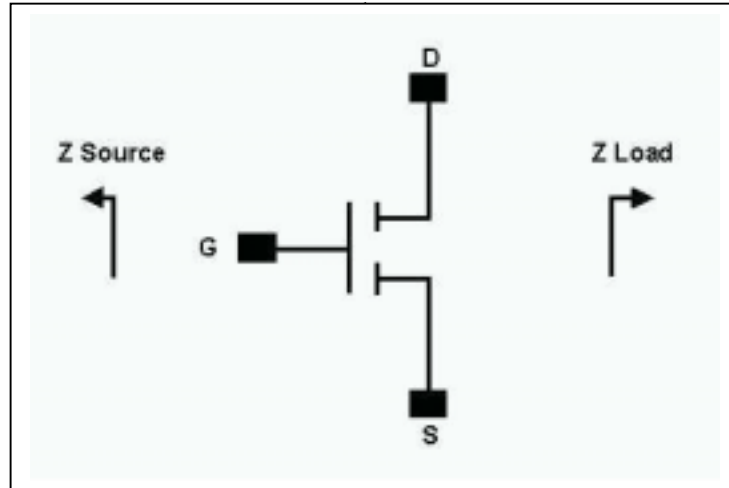








Impedance

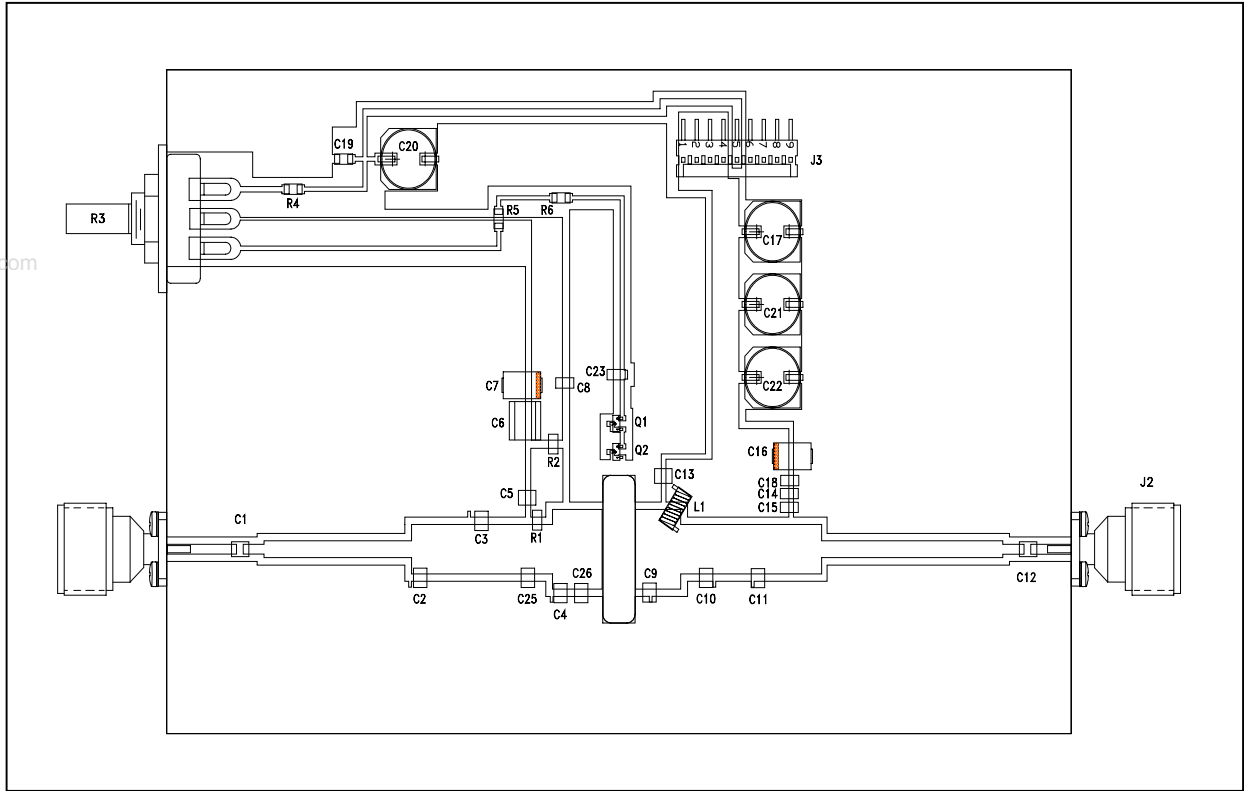


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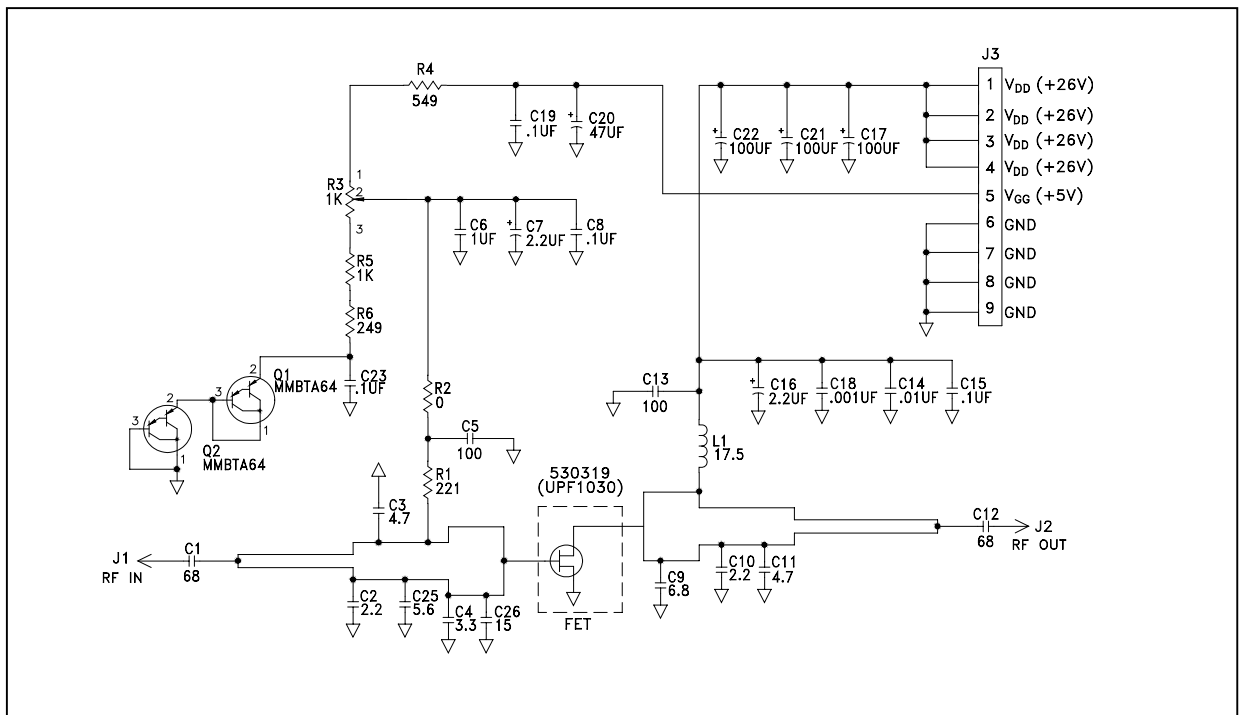
Frequency (MHz)	Z Source	Z Load
800	1.58 – j1.84	3.36 + j2.03
810	1.57 – j1.83	3.44 + j2.03
820	1.56 – j1.77	3.50 + j2.09
830	1.56 – j1.70	3.60 + j2.11
840	1.56 – j1.63	3.67 + j2.12
850	1.54 – j1.58	3.73 + j2.13
860	1.53 – j1.56	3.80 + j2.15
870	1.50 – j1.52	3.85 + j2.16
880	1.50 – j1.51	3.92 + j2.16
890	1.49 – j1.48	3.99 + j2.18
900	1.49 – j1.46	4.06 + j2.16

Note: $V_{DD} = 26V$, $I_{DQ} = 350mA$

Test Fixture Layout

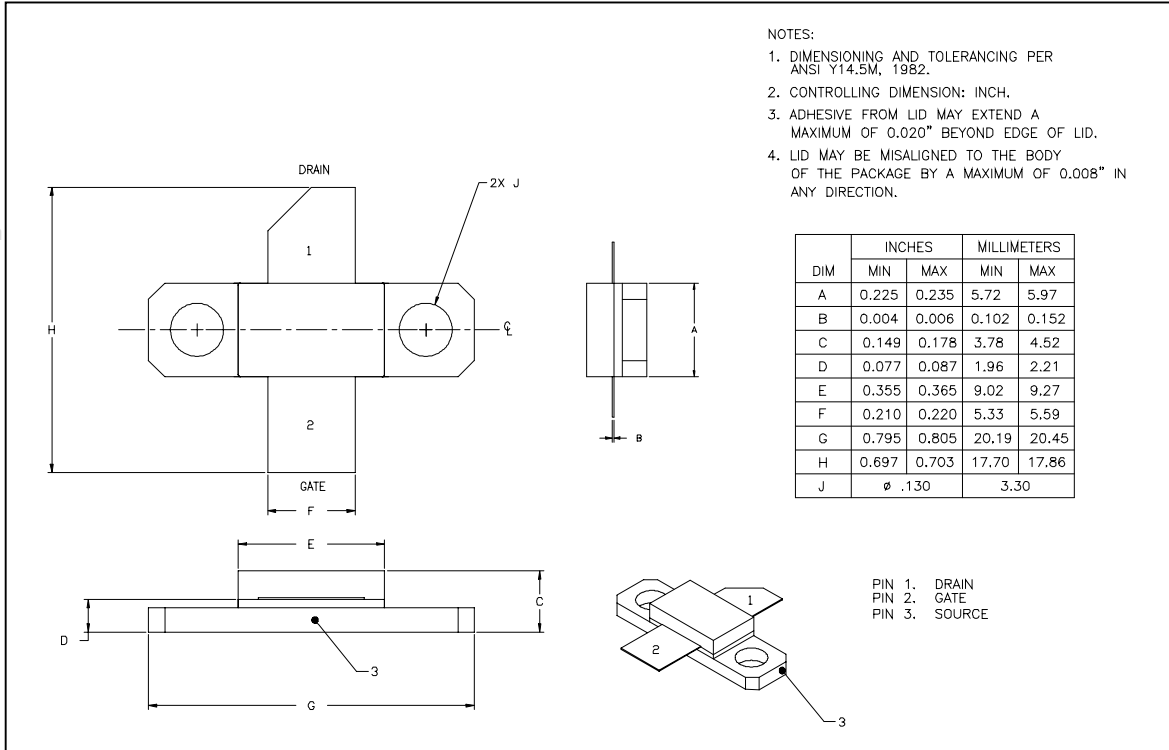


Test Fixture Schematic



Product Dimensions

UPF1030F -Package Number 440095



UPF1030P -Package Number 440134

